

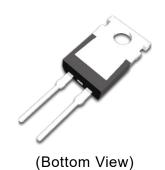
#### **Features**

#### Low Forward Voltage (VF)

- $\triangleright$ Shorter recovery time
- High speed switching
- High surge current capability  $\triangleright$
- Enabling higher frequency and increased  $\triangleright$ power density
- System efficiency improvement
- System cost and size savings due to the reduced cooling requirements

#### TO-220AC-2L





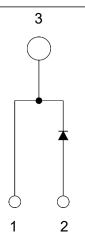
# **Applications**

- Power Factor Correction in SMPS
- Solar inverter
- **Uninterruptible Power Supply**
- **Motor Drives**
- AC/DC Converters

# **Pin Configuration**

# 3 ANJET 2 1

## **Circuit Diagram**



- 1: Cathode
- 2: Anode
- 3: Cathode

#### **Mechanical Characteristics**

- TO-220-2L package
- Pb-Free, Halogen Free, RoHS Compliant
- Packaging: Tube









# **Absolute Maximum Rating**

Symbol	Parameter	Value	Unit	Test Condition
$V_{RM}$	Repetitive peak reverse voltage	650	V	T <sub>C</sub> = 25°C
I <sub>F</sub>	Continuous forward current	2	Α	T <sub>C</sub> = 135°C
I <sub>FSM</sub>	Surge non-repetitive forward current	20 18	Α	$T_C$ = 25°C, tp=10ms, Sine half wave $T_C$ = 150°C, tp=10ms, Sine half wave
Tj	Junction temperature	175	°C	
T <sub>STG</sub>	Storage temperature	-55/+175	°C	

#### Thermal characteristics

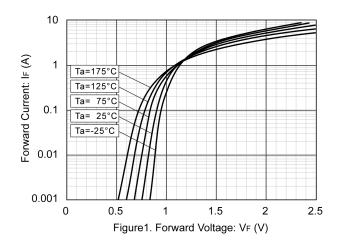
Symbol	Parameter	Min.	Тур.	Max.	Units
R <sub>th (JC)</sub>	Thermal resistance, junction-case	ı	1.3	ı	°C /W

#### **Electrical Characteristics**

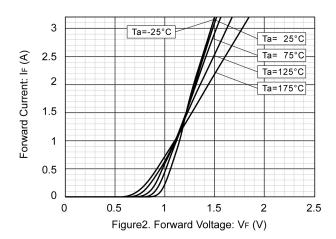
Symbol	Parameter	Min.	Тур.	Max.	Units	Test Condition
$V_{DC}$	DC blocking voltage	650	-	-	V	T <sub>j</sub> = 25 °C, I <sub>R</sub> =2.0mA
V <sub>F</sub>	Forward voltage	-	1.30 1.50 1.60	1.50 - -	V	$I_F = 2 \text{ A}, T_j = 25 \text{ °C}$ $I_F = 2 \text{ A}, T_j = 150 \text{ °C}$ $I_F = 2 \text{ A}, T_j = 175 \text{ °C}$
I <sub>R</sub>	Reverse current	-	1 20 50	50	μΑ	V <sub>R</sub> = 650 V, T <sub>j</sub> = 25 °C V <sub>R</sub> = 650 V, T <sub>j</sub> = 150 °C V <sub>R</sub> = 650 V, T <sub>j</sub> = 175 °C
Qc	Total capacitive charge	ı	6	-	nC	$V_R = 400 \text{ V}, T_j = 25 \text{ °C},$ $di/dt = 350 \text{ A/}\mu\text{s}$
t <sub>C</sub>	Switching time	-	11	-	ns	
С	Total capacitance	1	110 10	-	pF	V <sub>R</sub> = 1V, f = 1MHz, T <sub>j</sub> = 25°C V <sub>R</sub> = 650 V, f = 1MHz, T <sub>j</sub> = 25°C



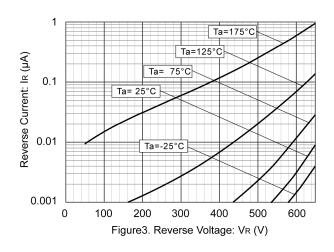
#### V<sub>F</sub> - I<sub>F</sub> Characteristics



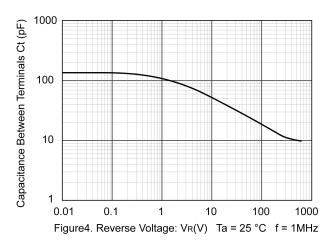
#### V<sub>F</sub> - I<sub>F</sub> Characteristics



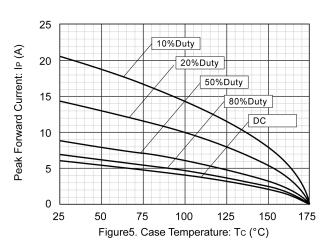
V<sub>R</sub> - I<sub>R</sub> Characteristics



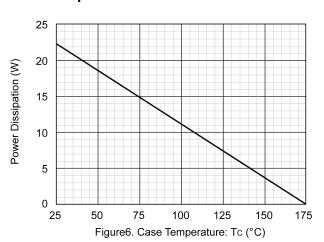
V<sub>R</sub> - C<sub>t</sub> Characteristics



#### Maximum I<sub>P</sub> -T<sub>C</sub> Characteristics

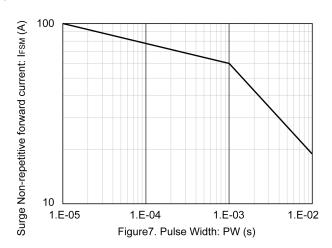


### **Power Dissipation**

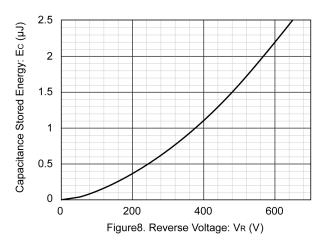




### I<sub>FSM</sub> - P<sub>W</sub> Characteristics

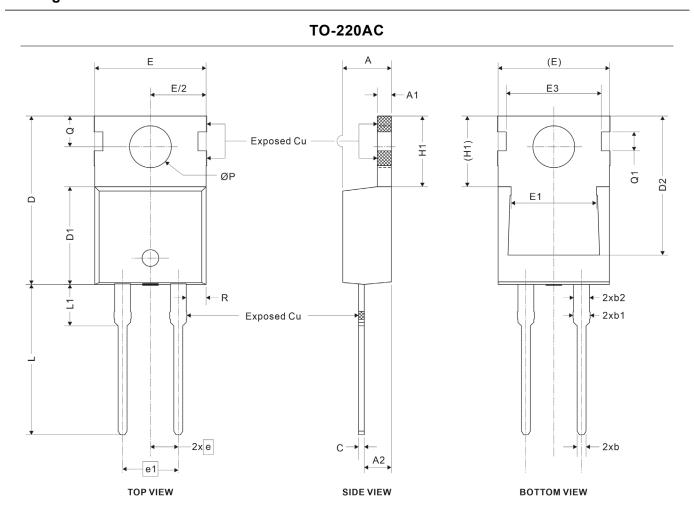


# E<sub>C</sub> - V<sub>R</sub> Characteristics





# **Package Outline**



# **Package Dimensions**

Symbol	Dimensions In Millimeters						
Symbol	Min.	NOM.	Max.				
Α	4.24	4.44	4.64				
A1	1.15	1.27	1.40				
A2	2.30	2.48	2.70				
b	0.70	0.80	0.90				
b1	1.20	1.55	1.75				
b2	1.20	1.45	1.70				
С	0.40	0.50	0.60				
D	14.70	15.37	16.00				
D1	8.82	8.92	9.02				
D2	12.63	12.73	12.83				
E	9.96	10.16	10.36				
E1	6.86	7.77	8.89				

Cumbal	Dimensions In Millimeters					
Symbol	Min.	NOM.	Max.			
E3	8.70REF.					
е	2.54BSC					
e1	5.08BSC					
H1	6.30	6.45	6.60			
L	13.47	13.72	13.97			
L1	3.60	3.80	4.00			
ØP	3.75	3.84	3.93			
Q	2.60	2.80	3.00			
Q1	1.73REF.					
R	1.82REF.					